

## UNISONIC TECHNOLOGIES CO., LTD

### UM6K1N Preliminary Power MOSFET

# SILICON N-CHANNEL MOSFET

#### ■ DESCRIPTION

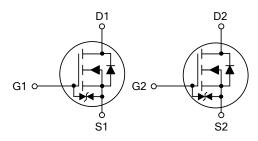
The UTC **UM6K1N** is a silicon N-channel MOSFET. it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate threshold voltage.

The UTC UM6K1N is suitable for switching and interfacing applications.



- \*  $R_{DS(on)}$ <8 $\Omega$  @  $V_{GS}$ =4V,  $I_D$ =10mA  $R_{DS(on)}$ <13 $\Omega$  @  $V_{GS}$ =2.5V,  $I_D$ =1mA
- \* High switching speed
- \* Low gate threshold voltage

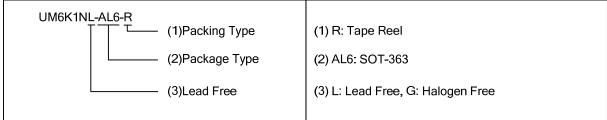
#### ■ SYMBOL



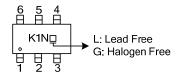
#### **■ ORDERING INFORMATION**

Orde	Daalaasa	Pin Assignment					Daaliaa		
Lead Free	Halogen Free	Package	1	2	3	4	5	6	Packing
UM6K1NL-AL6-R	UM6K1NG-AL6-R	SOT-363	S1	G1	D2	S2	G2	D1	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source



#### ■ MARKING



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#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	30	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current	Continuous	$I_D$	100	mA
Drain Current	Pulsed (Note 1)	I <sub>DM</sub>	200	mA
Power Dissipation (Note 2)	T <sub>C</sub> =25°C	$P_{D}$	150	mW
Channel Temperature		$T_CH$	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

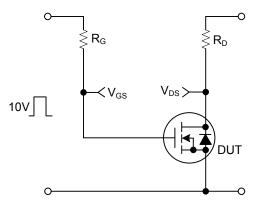
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Pw≤10µs, Duty cycle≤50%.
- 3. With each pin mounted on the recommended lands.

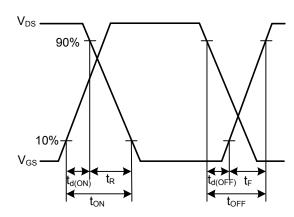
#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS		_					
Drain-Source Breakdown Voltage		$BV_DSS$	$I_D=10\mu A, V_{GS}=0V$	30			V
Drain-Source Leakage Current		$I_{DSS}$	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1.0	μΑ
Gate-Source Leakage Current	Forward		V <sub>GS</sub> =+20V, V <sub>DS</sub> =0V			+1	μΑ
	Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-1	μΑ
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V <sub>DS</sub> =3V, I <sub>D</sub> =100μA	8.0		1.5	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =4V, I <sub>D</sub> =10mA		5	8	Ω
			V <sub>GS</sub> =2.5V, I <sub>D</sub> =1mA		7	13	Ω
Forward Transfer Admittance		Y <sub>FS</sub>	V <sub>DS</sub> =3V, I <sub>D</sub> =10mA				mS
DYNAMIC PARAMETERS							
Input Capacitance		C <sub>ISS</sub>			13		pF
Output Capacitance		Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =5V, f=1.0MHz		9		pF
Reverse Transfer Capacitance		C <sub>RSS</sub>			4		pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		$t_{D(ON)}$			15		ns
Rise Time		$t_R$	V <sub>DD</sub> ≈5V, V <sub>GS</sub> =5V, I <sub>D</sub> =10mA, R <sub>GS</sub> =10Ω, R <sub>L</sub> =500Ω		35		ns
Turn-OFF Delay Time		t <sub>D(OFF)</sub>			80		ns
Fall-Time		$t_{F}$			80		ns

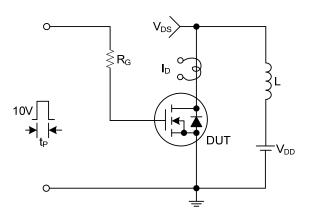
#### **■ TEST CIRCUITS AND WAVEFORMS**



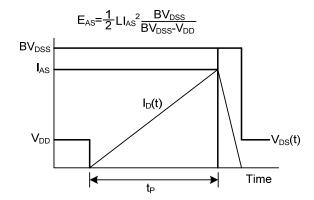
Resistive Switching Test Circuit



Resistive Switching Waveforms



**Unclamped Inductive Switching Test Circuit** 



Unclamped Inductive Switching Waveforms

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